

FORM PTO-892 (REV. 3-78)				U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	SERIAL NO.	GROUP ART UNIT	ATTACHMENT TO PAPER NUMBER	
					✓ 697830	258	2	
NOTICE OF REFERENCES CITED				✓ APPLICANT(S)	Huang et al			
U.S. PATENT DOCUMENTS								
*	DOCUMENT NO.		DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE	
A	4	916498	4/16/90	Berenz	357	22A		
B	4	821093	4/11/89	Iafrate et al	357	22A		
C	4	600932	7/15/86	Norris	357	22A		
D	4	652896	3/24/87	Das et al	357	22A		
E	5	008717	4/16/91	Bar-Joseph et al	357	22A		
F								
G								
H								
I								
J								
K								
FOREIGN PATENT DOCUMENTS								
*	DOCUMENT NO.		DATE	COUNTRY	NAME	CLASS	SUB-CLASS	PERTINENT SHTS. DWG. I PP. SPEC.
-L	1-199475	8/89	Japan	Matsumoto	357	22A		
-M	63-318165	12/88	Japan	Yamane	357	22A		
-N	59-119768	7/84	Japan	Ishikawa	357	22M0		
-O	59-4085	1/84	Japan	Mutou	357	22M0		
-P	1-94674	4/89	Japan	Nagami	357	22A		
-Q	1-128473	5/89	Japan	Izumi	357	22A		
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)								
R	IEEE Electron Device Letters, Vol. 10, No. 10, October 1989, "A 0.25- μ m Gate- Length Pseudomorphic HFET with 32-mW Output Power at 94 GHz" by Smith et al, P. 437-P. 439.							
T	IEEE Electron Device Letters, Vol. 11, No. 1, January 1990, "W-Band Low-Noise InAlAs/InGaAs Lattice-Matched HEMT's" by Chao et al, P. 59-P. 62.							
EXAMINER	DATE	Loke 10/16/91						
* A copy of this reference is not being furnished with this office action. (See Manual of Patent Examining Procedure, section 707.05 (a).)								